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MITSUBISHI SEMICONDUCTOR <GaAs FET>

MGFC42V5258

Unit: millimeters

0.6 + / - 0.15

(3)

20.4+/-0.2

13.4

(2) 8:5

24+/-0.3

(1)

5.2 - 5.8GHz BAND 16W INTERNALLY MATCHED GaAs FET

OUTLINE DRAWING

R1.25

R1.2

ZMIN

8.0+/-0.2

ZMIN

GF-18

DESCRIPTION

The MGFC42V5258 is an internally impedance-matched GaAs power FET especially designed for use in 5.2 - 5.8 GHz band amplifiers. The hermetically sealed metal-ceramic package guarantees high reliability.

FEATURES

Class A operation Internally matched to 50(ohm) system High output power P1dB = 16W (TYP.) @ f=5.2 - 5.8 GHz High power gain GLP = 10.5 dB (TYP.) @ f=5.2 - 5.8GHz High power added efficiency P.A.E. = 31 % (TYP.) @ f=5.2 - 5.8GHz

APPLICATION 5.2 - 5.8 GHz band power amplifier

QUALITY GRADE

RECOMMENDED BIAS CONDITIONS

VDS = 10 (V) ID = 4.5 (A) RG=25 (ohm)

ABSOLUTE MAXIMUM RATINGS

(Ta=25deg.C)

Symbol	Parameter	Ratings	Unit	
VGDO	Gate to drain voltage	-15	V	
VGSO	Gate to source voltage	-15	V	
ID	Drain current	15	А	
IGR	Reverse gate current	-40	mA	
IGF	Forward gate current	84	mA	
PT	Total power dissipation *1	78.9	W	
Tch	Channel temperature	175	deg.C	
Tstg	Storage temperature	-65 / +175	deg.C	

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(3): DRAIN

(2): SOURCE (FLANGE)

*1 : Tc=25deg.C

ELECTRICAL CHARACTERISTICS

(Ta=25deg.C)

Symbol	Parameter	Test conditions	Limits		Unit		
-			Min.	Тур.	Max.		
IDSS	Saturated drain current	VDS = 3V, $VGS = 0V$	-	9	12	А	
gm	Transconductance	VDS = 3V , ID = 4.4A	-	4	-	S	
VGS(off)	Gate to source cut-off voltage	VDS = 3V , ID = 80mA	-2	-3	-4	V	
P1dB	Output power at 1dB gain compression		41.5	42.5	-	dBm	
GLP	Linear power gain	VDS=10V, ID(RF off)=4.5A, f=5.2 - 5.8GHz	8	10.5	-	dB	
ID	Drain current]		4.5	-	Α	
P.A.E.	Power added efficiency		-	31	-	%	
Rth(ch-c)	Thermal resistance *1	delta Vf method	-	-	1.9	deg.C/W	
*1 : Channel-case							



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MGFC42V5258

5.2 - 5.8GHz BAND 16W INTERNALLY MATCHED GaAs FET

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